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b) Amendments to the Claims

--1. (Currently Amended) A method of ~~preparing porous~~ manufacturing material comprising the steps of:

(A) ~~making~~ contacting a solution containing a solvent, silicon and surfactant ~~be in contact~~ with a substrate for controlling alignment of an opposing surface of an overcoated layer thereon ~~having alignment control ability~~; and

(B) drying said coated substrate ~~made in contact with the solution~~ to remove the solvents contained in said solution and form a porous material having unaxially aligned channel structure in which the surfactant is held within the porous material.

2. (Original) A method according to claim 1, wherein silicon is contained in said solution in a state of compound.

3. (Cancelled)

4. (Currently Amended) A method of ~~preparing porous~~ manufacturing material, ~~materials,~~ comprising the steps of:

coating a substrate ~~having alignment control ability~~ capable of controlling alignment of an opposing surface of an overcoated layer thereon with a surfactant solution containing silicon alkoxide; and

drying said coated substrate to form a porous material with an unaxially aligned channel structure in which the surfactant is held within the porous material.

5. (Currently Amended) A method according to claim 4, wherein the step of coating the substrate is a step of selectively coating a desired portion of said

substrate with said solution in a desired pattern ~~patterned mesostructured silica with uniaxially aligned channel structure is formed by a step of coating a desired position of a substrate having alignment control ability with a surfactant solution containing silicon alkoxide in a desired shape and a step of drying said substrate~~ and, after the drying step, a patterned mesostructured silica is formed.

6. (Currently Amended) A method according to claim 4 or 5, wherein said substrate ~~with alignment control ability~~ is a silicon single crystal substrate having (110) orientation.

7. (Original) A method according to claim 4 or 5, wherein said substrate is a substrate whose surface is coated with a polymer compound film subjected to a rubbing process.

8. (Original) A method according to claim 4 or 5, wherein said substrate is a substrate whose surface is coated with a Langmuir-Blodgett film of polymer compound.

9. (Currently Amended) A method according to any one of claims 4 ~~to~~ ~~8~~ or 5, wherein the substrate is coated with the surfactant solution by a pen lithography method.

10. (Currently Amended) A method according to any one of claims 4 ~~to~~ ~~8~~ or 5, wherein the substrate is coated with the surfactant solution by an ink jet method.

11. (Currently Amended) A method according to any one of claims 4 ~~to~~ ~~8~~ or 5, wherein the substrate is coated with the surfactant solution by a dip coating method.

12. (Currently Amended) A method of ~~preparing porous~~ manufacturing material ~~materials~~, comprising the steps of:

coating a substrate ~~having alignment control ability~~ capable of controlling alignment of an opposing surface of an overcoated layer thereon with a solution of surfactant containing silicon alkoxides;

drying said coated substrate to form a porous material having unaxially aligned channel structure in which the surfactant is held within the porous material; and, thereafter,

removing the surfactant.

13. (Currently Amended) A method according to claim 12, wherein said step of coating said substrate with said solution is a step of selectively coating a desired ~~position~~ portion of said substrate with said solution in a desired ~~shape~~ pattern.

14. (Currently Amended) A method according to claim 12 or 13, wherein said substrate ~~with alignment control ability~~ is a silicon single crystal substrate having (110) orientation.

15. (Original) A method according to claim 12 or 13, wherein said substrate is a substrate whose surface is coated with a polymer compound film subjected to a rubbing process.

16. (Original) A method according to any one of claims 12 or 13, wherein said substrate is a substrate whose surface is coated with a Langmuir-Blodgett film of polymer compound.

17. (Currently Amended) A method according to any one of claims 12 ~~to 16~~ or 13, wherein said substrate is coated with said surfactant solution by a pen lithography method.

18. (Currently Amended) A method according to any one of claims 12 ~~to 16~~ or 13, wherein said substrate is coated with said surfactant solution by an ink jet method.

19. (Currently Amended) A method according to any one of claims 12 ~~to 16~~ or 13, wherein said substrate is coated with said surfactant solution by a dip coating method.

20. (Currently Amended) A method of ~~preparing porous~~ manufacturing material, ~~materials,~~ comprising the steps of:

(A) attaching a solution containing a solvent, silicon and surfactant to a substrate ~~having alignment control ability~~ for controlling alignment of an opposing surface of an overcoated layer thereon; and

(B) drying said substrate to which said solution is attached to remove ~~removing~~ the solvents contained in said solution and form a porous material having unaxially aligned channel structure in which the surfactant is held within the porous material ~~attached to said substrate~~.

21. (Original) A method according to claim 20, wherein silicon is contained in said solution in the form of compound.

22. (Original) A method according to claim 20, wherein silicon is contained in said solution as silicon alkoxides.

23. (New) A method of manufacturing material comprising the steps of:

(A) contacting a solution containing a solvent, silicon and surfactant with a substrate; and

(B) drying said substrate in contact with the solution to remove the solvent and form a porous material which has uniaxially aligned channel structure and pores in which the surfactant is held.

24. (New) A method according to Claim 1, further comprising the step of removing said surfactant.--